TOSHIBA GaAs Linear Integrated Circuit GaAs Monolithic

TG2401F

1.9 GHz Band TX Fronted IC PHS, Digital Cordless Telecommunication

Features

Common Block

• Positive voltage operation: $V_{DD1} = V_{DD2} = 3.0 \text{ V}$, $V_{DD3} = V_{DD4} = 3.6 \text{ V}$

Small package: HSOP20 (0.5 mm pin pitch)

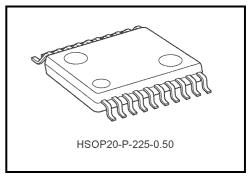
Power Amp. Block

• High power Gain: Gp = 32dB (min)

Antenna Switch Block

• Low insertion Loss: Loss = 0.8dB (typ.)

• High isolation: ISL = 25dB (typ.)



Weight: 0.058 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
	V _{DD} (Note 1)		V
Supply voltage	V _{GG} (Note 2)	4	V
	V _C (Note 3)	3.65	V
Input power	Pi	1	mW
Power dissipation	P _d (Note 4)	4	W
Operating temperature range	T _{opr} (Note 5)	-40 to 85	°C
Storage temperature range	T _{stg}	-55 to 150	°C

Note 1: $V_{DD} = V_{DD1} = V_{DD2} = V_{DD3} = V_{DD4} = V_{DD}$ (SW)

Note 2: $V_{GG} = V_{GG3} = V_{GG4}$

Note 3: $V_C = V_{C1} = V_{C2}$

Note 4: When mounted on a Teflon board (52 mm \times 43 mm \times 0.4 mm) that is fixed to an aluminum plate. (Ta = 25°C)

Note 5: Not intended to guarantee the following electrical characteristics, which were measured at Ta = 25°C.

Caution

This device is electrostatic sensitivity. Please handle with caution.

Electrical Characteristics

[Power Amp, Block]

 $(V_{DD} = V_{DD2} = 3 \text{ V}, V_{DD3} = V_{DD4} = 3.6 \text{ V}, V_{GG} = (Note6), f = 1.893 \text{ GHz}, Ta = 25^{\circ}\text{C}, Zg = ZI = 50 \ \Omega)$

[ANT-SW Block]

 $(V_{DD (SW)} = 3 \text{ V, f} = 1.893 \text{ GHz, Ta} = 25^{\circ}\text{C})$

Characteristics	Symbol	Test Circuit	Test Condition		Min	Тур.	Max	Unit
Operating frequency	f	_	_		1.893	_	1.920	GHz
Supply current (PA)	It	_	P _o = 20.5dBmW, P _i = adjust		_	_	170	mA
Gate current (PA)	I _{GG}	_	V _{GG} = 2 V		_	_	2	mA
Power gain	Gp	_	$P_0 = 20.5 dBmW$		32	_	38	dB
Output deviation	ΔP_o	_	f = 1.893,1.920 GHz, P _i =fixed		_	0.5	1.0	dB
Input VSWR	VSWRin	_	$P_i = -30 dBmW$		_	_	3.0	_
Adjacent channel leakage power ratio	ACP (1)	_	D odiust	$\Delta f = 600 \text{ kHz}$		_	-55	dB
Adjacent channel leakage power ratio	ACP (2)	_		$\Delta f = 900 \text{ kHz}$	_	_	-60	dB
Harmonics	2f0	_	D 00 5 ID W D	D. adiiyat	_	_	-30	dB
narmonics	enonics $P_0 = 20.5 dBmW, P_i = adjust$	P _i = aujusi	_	_	-30	dB		
Load mismatch	_	_	$\begin{split} &\text{V}_{DD3,~4}=4.2~\text{V},~\text{V}_{GG}=\text{adjust},\\ &\text{P}_{o}=20.5\text{dBmW},~\text{P}_{i}=\text{adjust},\\ &\text{Z}g=50~\Omega\\ &\text{VSWR Load}=6\text{:}1~\text{all phase} \end{split}$		No degradation			
Stability	_	_	$\begin{array}{c} V_{DD3,\;4}=3.24.2\;\text{V},\\ V_{C1}=3\;\text{V},\;V_{GG}=\text{adjust},\\ P_i=-15\text{dBmW}\;\text{to}\;-10\text{dBmW},\\ Zg=50\;\Omega\\ \text{VSWR}\;\text{Load}=6\text{:}1\;\text{all}\;\text{phase} \end{array}$		No spurious			
0		TX	V _{C1} = 3 V, V _{C2} =	0 V	_	_	0.04	mA
Supply current (SW)	ıDD	RX	V _{C1} = 0 V, V _{C2} = 3 V		_	_	0.04	mA
Control current (SW)	I _{rx}	TX	V _{C1} = 3 V, V _{C2} =	0 V	_	_	0.04	mA
Control current (Svv)	I _{tx}	RX	V _{C1} = 0 V, V _{C2} = 3 V		_	_	0.04	mA
Insertion Loss	L _{OSS}	RX	$V_{C1} = 0 \text{ V}, V_{C2} = 3 \text{ V},$ $P_{i} \text{ (SW)} = 0 \text{dBmW}$			0.8	1.0	dB
Isolation	ISL TX	TX	$V_{C1} = 3 \text{ V}, V_{C2} = 0 \text{ V},$ $P_{O} = 20.5 \text{dBmW}$		20	25	_	dB
		RX	$V_{C1} = 0 \text{ V}, V_{C2} = 0 \text{ V}$ $P_{i \text{ (SW)}} = 0 \text{dBmW}$	3 V,	10	15	_	dB

- (1) The P₀ in this technical data includes insertion Loss for ANT-SW.
- (2) Stability's load condition is that SHORT STAB join to ANT (Pin No.11) and all phase.
- (3) All test for ELCTRICAL CHARACTERISTICS bases on measure with following "RF TES BOARD".
- (4) Control current is separated by TX and RX mode. TX control current is I_{TX} , RX control current is I_{TX} .

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(5) Operation mode

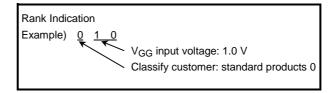
	RX Mode	TX Mode
VC1	0 ± 0.2 V	3 + 0.4 V 3 - 0.2 V
V _{C2}	$\begin{array}{c} 3 + 0.4 \ V \\ 3 - 0.2 \ V \end{array}$	0 ± 0.2 V

 $V_{DD (SW)} = 3 \pm 0.05 V$

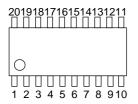
- (6) Input signal is modulated to $\pi/4QPSK$ ($\alpha=0.5$). Bit rate is 384 kbps.
- (7) 1/2 duty operation.

Note 6: Classify VGG Rank (UNDECIDED)

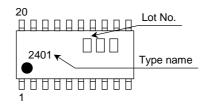
Rank	V _{GG} Condition	
000	0 V	
010	1 V	
020	2 V	
030	2.8 V	



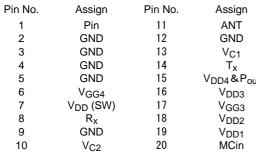
Pin Assignment (top view)

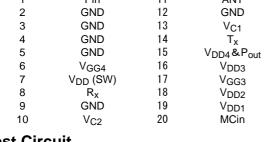


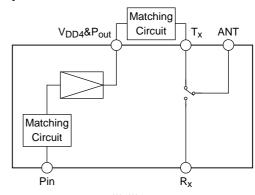
Marking



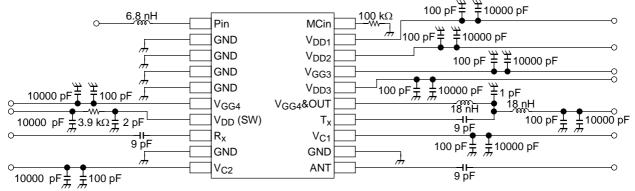
Equivalent Circuit











Caution

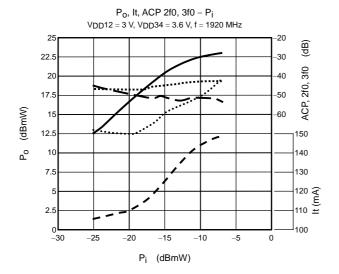
The circuits and measurements contained in this document are given only in the context of as examples of applications for these products.

Moreover, these example application circuits are not intended for mass production, since the high-frequency characteristics (the AC characteristics) of these devices will be affected by the external components which the customer uses, by the design of the circuit and by various other conditions.

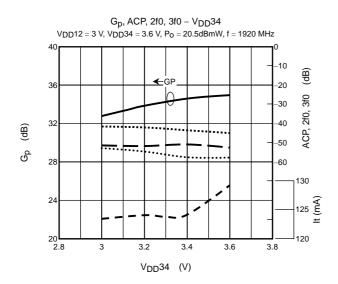
It is the responsibility of the customer to design external circuits which correctly implement the intended application, and to check the characteristics of the design.

TOSHIBA assume no responsibility for the integrity of customer circuit designs or applications.

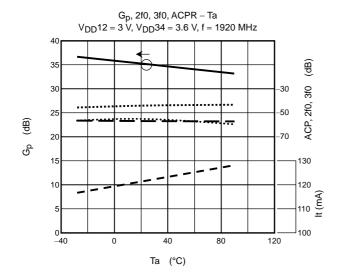
Curve Data





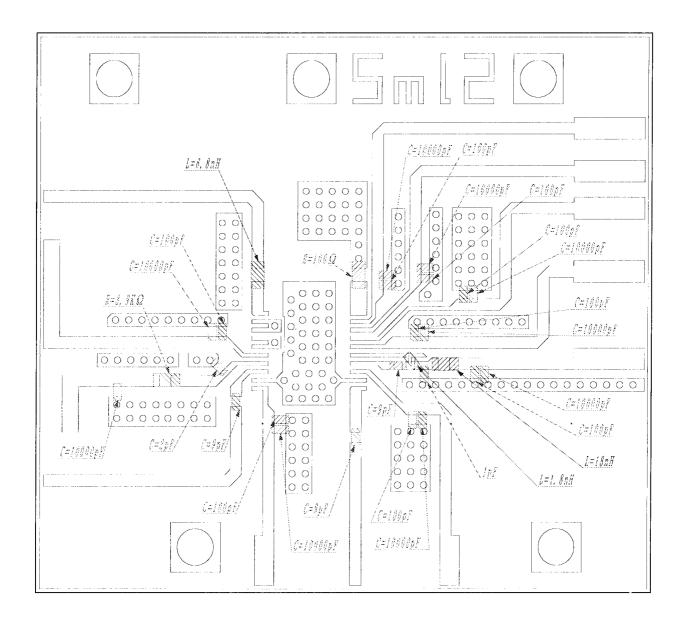








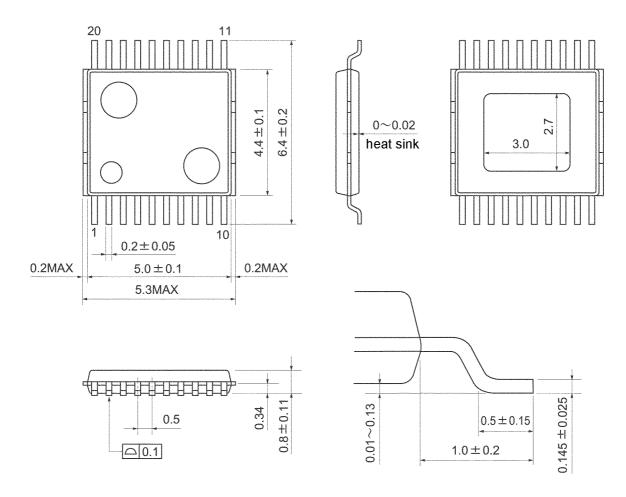
RF Test Board



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Package Dimensions

HSOP20-P-225-0.50 Unit: mm



Weight: 0.058 g (typ.)

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RESTRICTIONS ON PRODUCT USE

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